

1. (Currently Amended) An integrated circuit structure comprising:
a substrate;
first-type transistors on said substrate, wherein said first-type transistors comprise first gate conductors and first spacers adjacent said first gate conductors; and
second-type transistors on said substrate, wherein said second-type transistors comprise second gate conductors, said first spacers adjacent said second gate conductors,
an etch stop layer on said first spacers, and second spacers adjacent said first spacers on said etch stop layer.
2. (Original) The integrated circuit structure in claim 1, wherein said second spacers are only adjacent said first spacers that are adjacent said second gate conductors, and said second spacers are not adjacent said first spacers that are adjacent said first gate conductors.
3. (Currently Amended) The integrated circuit structure in claim 1, ~~further comprising an etch stop layer positioned between said first spacers and said second spacers~~, wherein said etch stop layer is only on said first spacers that are adjacent said second gate conductors and said etch stop layer is not on said first spacers that are adjacent said first gate conductors.
4. (Original) The integrated circuit structure in claim 1, further comprising:
first-type impurity implants in areas of said substrate adjacent said first spacers of said first gate conductors; and

second-type impurity implants in areas of said substrate adjacent said second spacers of said second gate conductors.

5. (Original) The integrated circuit structure in claim 4, wherein said first-type impurity is spaced closer to said first gate conductors than said second-type impurity is spaced from said second gate conductors.
6. (Original) The integrated circuit structure in claim 4, wherein said first-type impurity and said second-type impurity comprises source/drain impurities.
7. (Original) The integrated circuit structure in claim 1, wherein said first-type transistors comprise n-type field effect transistors (NFETs) and said second-type transistors comprise p-type field effect transistors (PFETs).
8. (Currently Amended) An integrated circuit structure comprising:
 - a substrate;
 - first-type transistors on said substrate, wherein said first-type transistors comprise first gate conductors and first spacers adjacent said first gate conductors; and
 - second-type transistors on said substrate, wherein said second-type transistors comprise second gate conductors, said first spacers adjacent said second gate conductors, an etch stop layer on said first spacers, and second spacers on said etch stop layer;
 - first-type impurity implants in areas of said substrate completely outside of said first spacers of said first gate conductors; and

second-type impurity implants in areas of said substrate completely outside of said second spacers of said second gate conductors.

9. (Currently Amended) The integrated circuit structure in claim 8, wherein said second spacers are only ~~adjacent~~ proximate said first spacers that are adjacent said second gate conductors and said second spacers are not ~~adjacent~~ proximate said first spacers that are adjacent said first gate conductors.
10. (Original) The integrated circuit structure in claim 8, wherein said etch stop layer is only on said first spacers that are adjacent said second gate conductors and said etch stop layer is not on said first spacers that are adjacent said first gate conductors.
11. (Cancelled).
12. (Currently Amended) The integrated circuit structure in claim ~~44~~ 8, wherein said first-type impurity is spaced closer to said first gate conductors than said second-type impurity is spaced from said second gate conductors.
13. (Currently Amended) The integrated circuit structure in claim ~~44~~ 8, wherein said first-type impurity and said second-type impurity comprises source/drain impurities.

14. (Original) The integrated circuit structure in claim 8, wherein said first-type transistors comprise n-type field effect transistors (NFETs) and said second-type transistors comprise p-type field effect transistors (PFETs).

15-25 (Cancelled).